

L Number	Hits	Search Text	DB	Time stamp
13	900	conduct\$6 and In near5 Ga near5 N	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/21 16:25
14	75	(conduct\$6 with (In near5 Ga near5 N))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/21 16:25
15	69	(conduct\$6 with (In near5 Ga near5 N))	USPAT; EPO; JPO; DERWENT	2004/04/21 16:26
16	3	((conduct\$7 near1 (layer or region or medium)) with (In near5 Ga near5 N))	USPAT; EPO; JPO; DERWENT	2004/04/21 16:27
-	131	(nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad\$5 near layer) and indium and substrate and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/21 16:24
-	20	(nitride near semiconductor) and ((buffer near layer) with indium) and (active near layer) and (clad\$5 near layer) and substrate and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/06 11:28
-	28	(nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad\$5 near layer) and indium and substrate and electrode and absorb\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:52
-	21	((nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad\$5 near layer) and indium and substrate and electrode and absorb\$6) not ((nitride near semiconductor) and ((buffer near layer) with indium) and (active near layer) and (clad\$5 near layer) and substrate and electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:52
-	6	(laser near chip) and (photoelectric or (photo adj electric)) and block\$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 17:42
-	160	(laser near semiconductor) and (photoelectric or (photo adj electric)) and block\$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/11 11:18
-	14	(laser near semiconductor) and (photoelectric or (photo adj electric)) and block\$6 and buffer and substrate and (laser near3 chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 17:46
-	171	(laser near semiconductor) and (photoelectric or (photo adj electric) or (photodetector) (photodiode) or (photo adj detector) or (photo adj diode)) and block\$6 and buffer and substrate and (laser near3 chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 07:00
-	72	(semiconductor near laser near3 chip) and (photoelectric or (photo adj electric) or (photodetector) (photodiode) or (photo adj detector) or (photo adj diode)) and block\$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 07:03

L Number	Hits	Search Text	DB	Time stamp
13	900	conduct\$6 and In near5 Ga near5 N	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/21 16:25
14	75	(conduct\$6 with (In near5 Ga near5 N))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/21 16:25
15	69	(conduct\$6 with (In near5 Ga near5 N))	USPAT; EPO; JPO; DERWENT	2004/04/21 16:26
16	3	((conduct\$7 near1 (layer or region or medium)) with (In near5 Ga near5 N))	USPAT; EPO; JPO; DERWENT	2004/04/21 16:52
17	3504	(conduct\$7 near1 (layer or region or medium)) and substrate and clad\$6	USPAT; EPO; JPO; DERWENT	2004/04/21 16:48
18	42	(conduct\$7 near1 (layer or region or medium)) and substrate and clad\$6 and (In near5 Ga near5 N)	USPAT; EPO; JPO; DERWENT	2004/04/21 16:48
19	14	((conduct\$7 near1 (layer or region or medium)) same (In near5 Ga near5 N))	USPAT; EPO; JPO; DERWENT	2004/04/21 16:52
20	88	In"x"GaN1-x"N	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/21 16:55
21	3	In"x"GaN1-x"N and (conduct\$7 near1 (layer or region or medium)) and substrate and clad\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/21 16:55